

EAST - [10633149.wsp:1]

File View Edit Tools Window Help

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 L1: (2) c-Si and amorphous near silicon and trench and etch near stop
 L2: (1) 'c-Si' and etch near stop near layer and amorphous near silicon and trench
 L3: (387) substrate and etch near stop near layer and amorphous near silicon and trench
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 c-Si and amorphous near si\$5 and trench and etch near stop
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DBs US-PG Plurals

Default operator: ☒ Highlight all hit terms initially

substrate and etch near stop near layer and amorphous near silicon and trench

BRS form IS&R form Image Text

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20040266216 A1	20041230	11	Method for improving uniformity in deposited low k dielectric material	438/778	438/782	
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20040266053 A1	20041230	28	METHOD OF UTILIZING A TOP CONDUCTIVE LAYER IN ISOLATING	438/94		
3	<input type="checkbox"/>	<input type="checkbox"/>	US 20040264240 A1	20041230	16	Protective layers for MRAM devices	365/158		
4	<input type="checkbox"/>	<input type="checkbox"/>	US 20040262635 A1	20041230	73	Three-dimensional integrated circuit structure and method of making same	257/199		
5	<input type="checkbox"/>	<input type="checkbox"/>	US 20040256651 A1	20041223	17	Extendible process for improved top oxide layer for DRAM array and the gate	257/296	257/330; 257/331;	
6	<input type="checkbox"/>	<input type="checkbox"/>	US 20040251513 A1	20041216	13	Shallow trench isolation structure with low sidewall capacitance for high speed	257/510	257/513; 438/221;	
7	<input type="checkbox"/>	<input type="checkbox"/>	US 20040246311 A1	20041209	714	Inkjet printhead with heater element close to drive circuits	347/57		
8	<input type="checkbox"/>	<input type="checkbox"/>	US 20040245637 A1	20041209	19	Method for supporting a bond pad in a multilevel interconnect structure and	257/758		
9	<input type="checkbox"/>	<input type="checkbox"/>	US 20040245586 A1	20041209	38	Microelectromechanical systems having trench isolated contacts, and methods for	257/414	257/417; 438/48;	
10	<input type="checkbox"/>	<input type="checkbox"/>	US 20040222495 A1	20041111	44	Diffused extrinsic base and method for fabrication	257/565		
11	<input type="checkbox"/>	<input type="checkbox"/>	US 20040222486 A1	20041111	22	BICMOS TECHNOLOGY ON SOI SUBSTRATES	257/507	257/517; 257/526;	